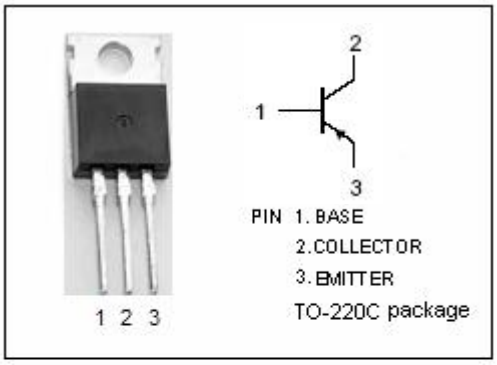
SPTECH Silicon PNP Power Transistor 2N6491

DESCRIPTION

- DC Current Gain Specified to 15 Amperes-
  : h_{FE} =20-150@ I_C= -5.0Adc
  =5.0(Min)@ I_C= -5Adc
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -80Vdc(Min)
- Complement to Type 2N6488



APPLICATIONS

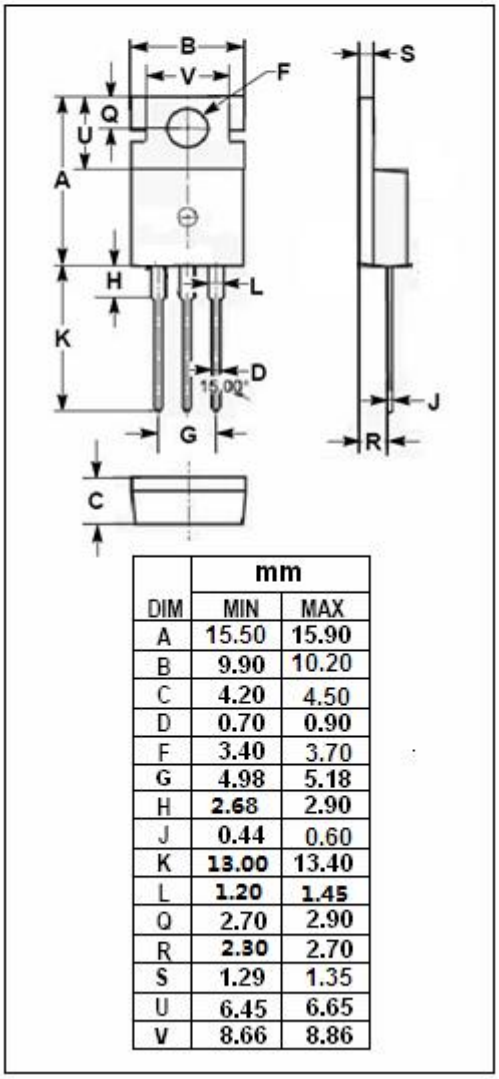
- Designed for use in general-purpose amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-90	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current	-5	A
P_C	Collector Power Dissipation @ T_C=25℃	75	W
	Collector Power Dissipation @ T_a=25℃	1.8	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.67	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	70	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ;I_B=0	-80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A		-1.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -15A ; I_B = -5.0A		-3.5	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	I_C= -5A ; V_{CE}= -4V		-1.3	V
$V_{BE(on)-2}$	Base-Emitter On Voltage	I_C= -15A ; V_{CE}= -4V		-3.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -40V;I_B=0		-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0		-1.0	mA
h_{FE-1}	DC Current Gain	I_C= -5A ; V_{CE}= -4V	20	150	
h_{FE-2}	DC Current Gain	I_C= -15A ; V_{CE}= -4V	5		
f_T	Current-Gain—Bandwidth Product	I_C= -1.0A ; V_{CE}= -4V; f_{test}=1.0MHz	5.0		MHz